



ASMD 036AUS

#9
Amend A
D Small's Loop
PATENT
1-29-03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : SOPHIE ET AL.

Appl. No. : 09/975,466

Filed : October 9, 2001

For : IN SITU REDUCTION OF
COPPER OXIDE PRIOR TO
SILICON CARBIDE
DEPOSITION

) Group Art Unit 2813

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) (Date)

) Adeel S. Akhtar, Reg. No. 41,394

Examiner : Kielin, E.

Amendment and Response to Office Action

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

The present paper is submitted in response to the Office Action mailed on October 15, 2002. Applicants respectfully request that the Examiner enter the following amendments and consider the subsequent remarks.

In the Claims

Please cancel Claim 29.

Please amend Claims 1, 5, 8 and 28 to read as follows:

a¹ SUB B1
1. (Amended) A process for producing an integrated circuit comprising reducing copper oxide on a substrate by exposure to one or more stable organic reducing agents prior to deposition of a layer comprising silicon carbide.

a²
5. (Amended) The process of Claim 4, wherein the organic reducing agent is selected from the group consisting of primary alcohols, secondary alcohols, tertiary alcohols, polyhydroxyalcohols, cyclic alcohols, and halogenated alcohols.

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